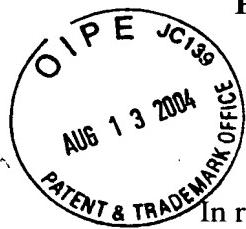


IFW

Patent



Customer No. 31561
Docket No. 13114-US-PA
Application No.: 10/709,719

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Applicant : Tang
Application No. : 10/709,719
Filed : 2004/5/25
For : MULTI-GATE DRAM WITH DEEP-TRENCH CAPACITOR
AND FABRICATION THEREOF
Examiner :
Art Unit : 2818

INFORMATION DISCLOSURE STATEMENT

ASSISTANT COMMISSIONER FOR PATENTS
Arlington, VA22202

Enclosed is a PTO Form 1449 listing 2 reference(s), copy of which is attached.
Applicant submits the reference(s) in compliance with his duty of disclosure pursuant to
37 CFR § 1.56 and 1.97. The Examiner is requested to make the citation(s) of official
record.

This IDS is being submitted before the first Office Action. Thus, it is believed no
fee is due.

The submission of the reference(s) should not be interpreted as admitting
them as prior art.

Respectfully Submitted,
JIANQ CHYUN Intellectual Property Office

Date: August 11, 2004

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICATION		ATTY. DOCKET NO.:13114-US-PA	APPLICATION NO.: 10/709,719
		APPLICANT: Tang	
		FILING DATE: May 25, 2004	GROUP 2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	Radens et al., "A 0.135 μm ² 6F ² Trench-Sidewall Vertical Device Cell for 4Gb/16Gb DRAM", 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 80-81.
	Mandelman et al., "Challenges and future directions for the scaling of dynamic random-access memory (DRAM), in IBM J. RES. & DEV. Vol. 46 No. 2/3 March/ May 2002, pp. 187-212.

EXAMINER	DATE CONSIDERED

EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEST COMMUNICATION TO APPLICANT.